

CEP655N/CEB655N CEI655N/CEF655N

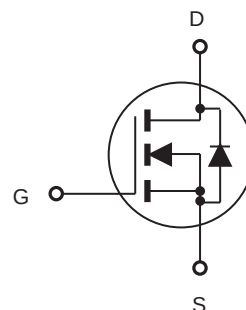
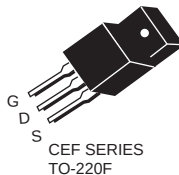
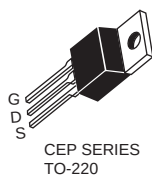
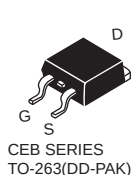
N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP655N	150V	0.153Ω	15A	10V
CEB655N	150V	0.153Ω	15A	10V
CEI655N	150V	0.153Ω	15A	10V
CEF655N	150V	0.153Ω	15A ^d	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-262 package & TO-220F full-pak for through hole.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263/262	TO-220F	
Drain-Source Voltage	V _{DS}	150		V
Gate-Source Voltage	V _{GS}	±25		V
Drain Current-Continuous	I _D	15	15 ^d	A
Drain Current-Pulsed ^a	I _{DM} ^e	60	60 ^d	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P _D	83	39	W
		0.56	0.26	W/°C
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 175		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	1.8	3.8	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W

[查询"CEF655N"供应商](#)

CEP655N/CEB655N CEI655N/CEF655N

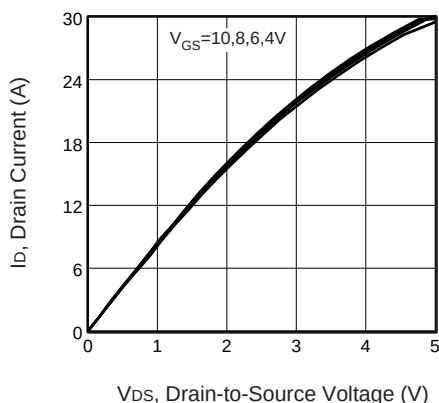


Figure 1. Output Characteristics

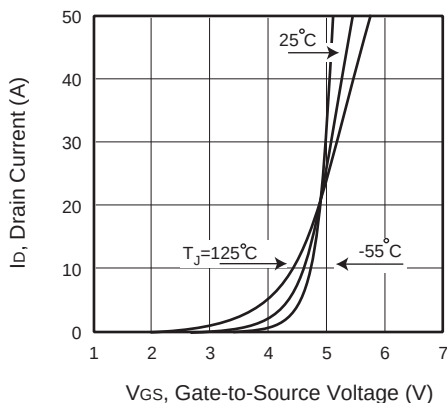


Figure 2. Transfer Characteristics

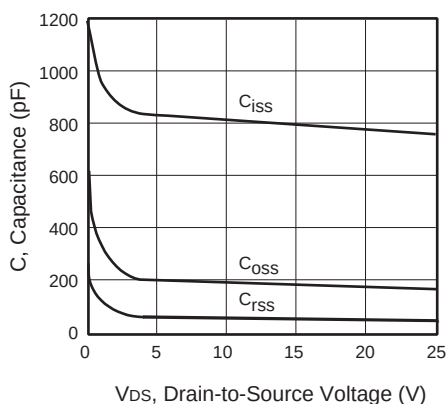


Figure 3. Capacitance

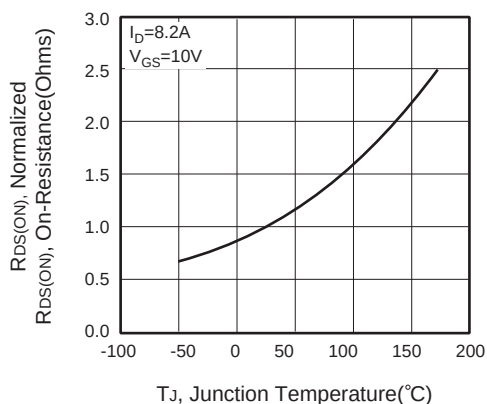


Figure 4. On-Resistance Variation with Temperature

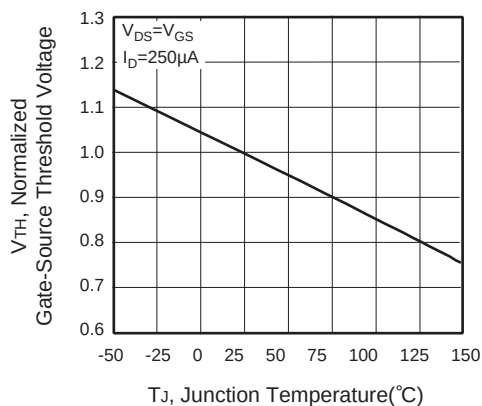


Figure 5. Gate Threshold Variation with Temperature

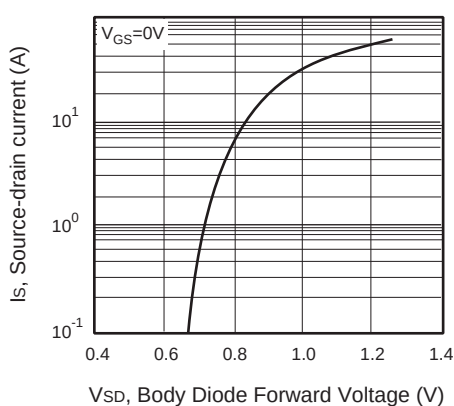


Figure 6. Body Diode Forward Voltage Variation with Source Current

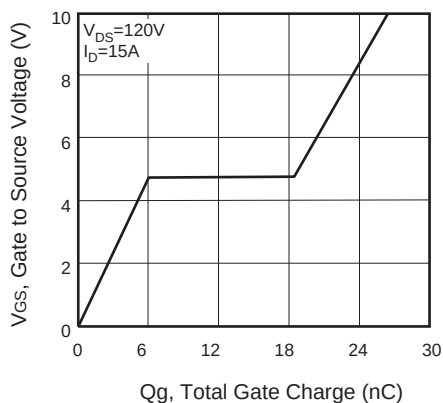


Figure 7. Gate Charge

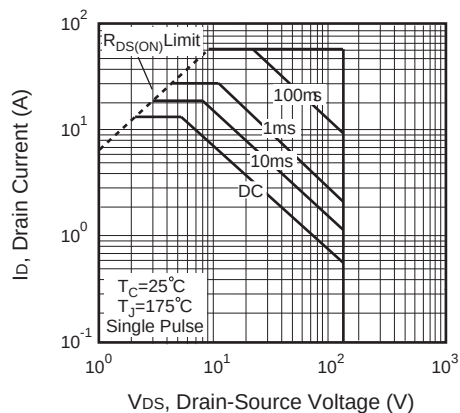


Figure 8. Maximum Safe Operating Area

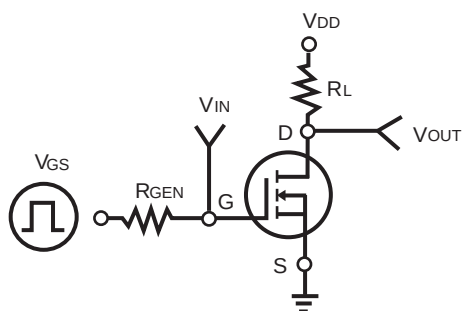


Figure 9. Switching Test Circuit

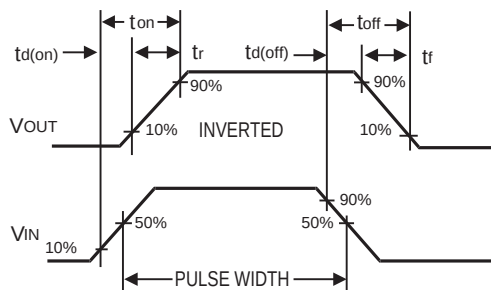


Figure 10. Switching Waveforms

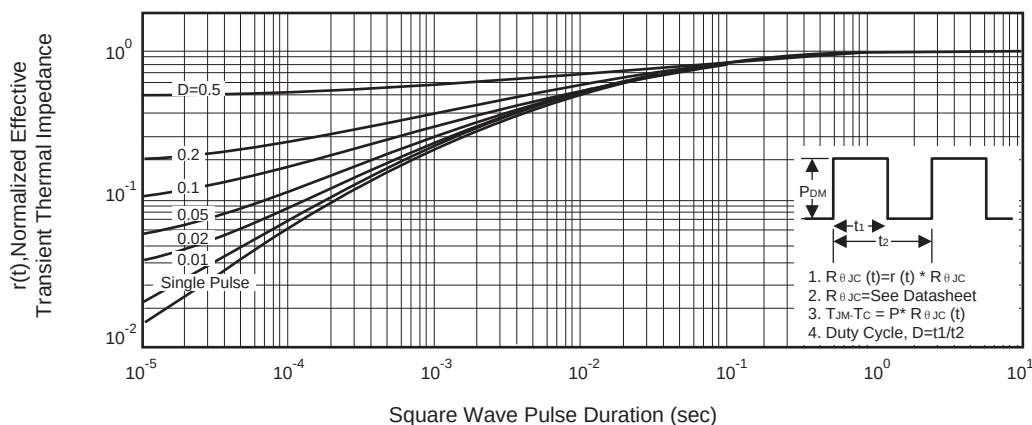


Figure 11. Normalized Thermal Transient Impedance Curve